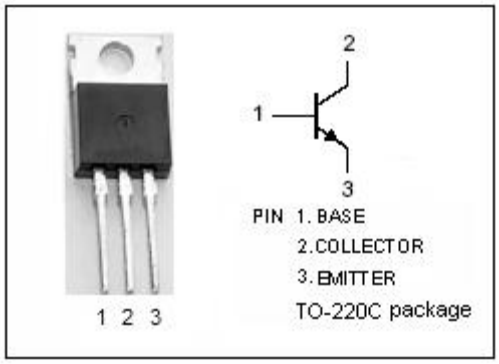
SPTECH Silicon NPN Power Transistor

DESCRIPTION

- Collector-Emitter Sustaining Voltage-: $V_{CEO(SUS)}$= 250V(Min)
- DC current gain -
  : h_{FE} = 50 (Min) @I_C= 0.5 A
  : h_{FE} = 10 (Min) @I_C= 2.0 A
- Complement to Type MJE15033G



APPLICATIONS

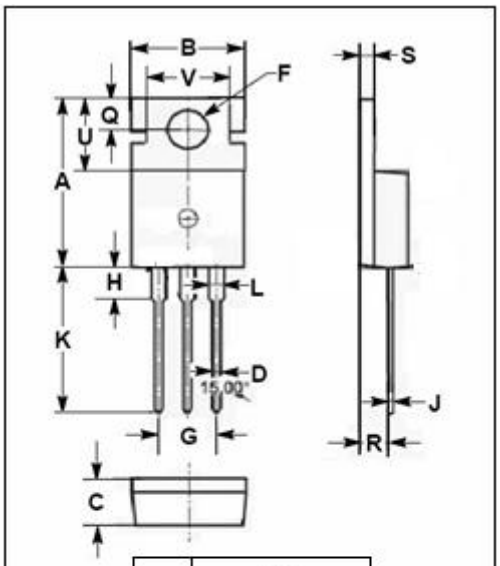
- Designed for use as high–frequency drivers in audio amplifiers.

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	8	A
I_{CM}	Collector Current-Peak	16	A
I_B	Base Current	2	A
P_C	Collector Power Dissipation @T_a=25℃	2	W
	Collector Power Dissipation @T_C=25℃	50	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.5	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

SPTECH Silicon NPN Power Transistors

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA ;I_B= 0	250		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A ;I_B= 0.1A		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 1A ; V_{CE}= 5V		1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 150V; I_E= 0		10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0		10	μA
h_{FE-1}	DC Current Gain	I_C= 0.5A ; V_{CE}= 5V	50		
h_{FE-2}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	50		
h_{FE-3}	DC Current Gain	I_C= 2A ; V_{CE}= 5V	10		
f_T	Current Gain-Bandwidth Product	I_C= 0.5A; V_{CE}= 10V; f_{test}= 1.0MHz	30		MHz